

**isc N-Channel MOSFET Transistor**

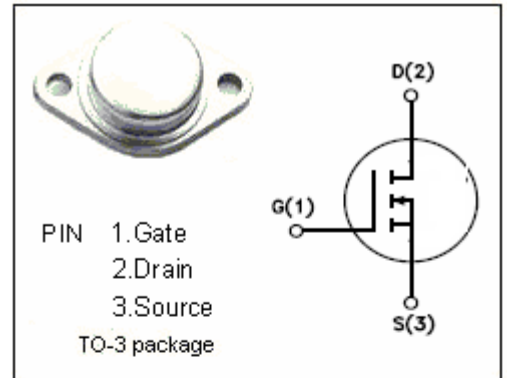
**2N6767**

**DESCRIPTION**

- VGS Rated at ±20V
- Silicon Gate for fast switching speeds
- IDSS、RDS(ON) specified at elevated temperature
- Low drive requirements

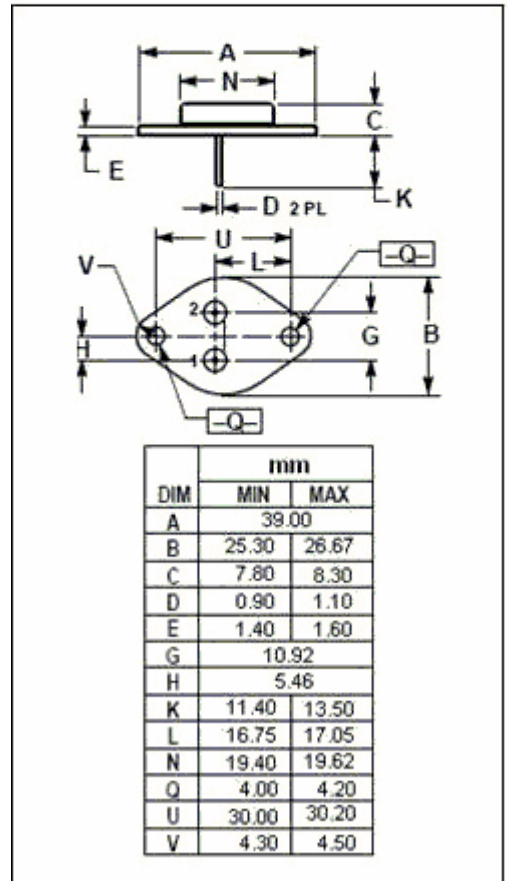
**APPLICATIONS**

designed for high power ,high speed application ,such as switching applies,UPS,AC and DC motor controls , relay and high energy pulse circuits.



**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	ARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	350	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-continuous@ TC=37°C	12	A
P <sub>tot</sub>	Total Dissipation@TC=25°C	150	W
T <sub>j</sub>	Max. Operating Junction Temperature	-55~150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	0.83	°C/W

**isc N-Channel Mosfet Transistor****2N6767****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	350		V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA	2	4	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 7.75A		0.4	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = 20V; V <sub>DS</sub> = 0		100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 350V; V <sub>GS</sub> = 0		1	mA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> = 12A; V <sub>GS</sub> = 0		1.6	V